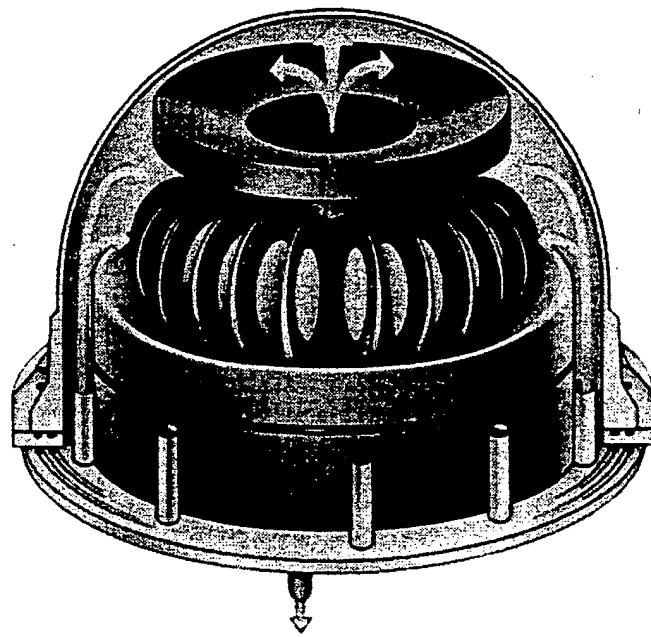


# HANDBOOK OF THIN-FILM DEPOSITION PROCESSES AND TECHNIQUES

Principles, Methods, Equipment  
and Applications



Edited by  
**Klaus K. Schuegraf**

**NOYES PUBLICATIONS**

**Appendix B**

Goldwasser *et al.*  
Application No.: 08/847,967

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